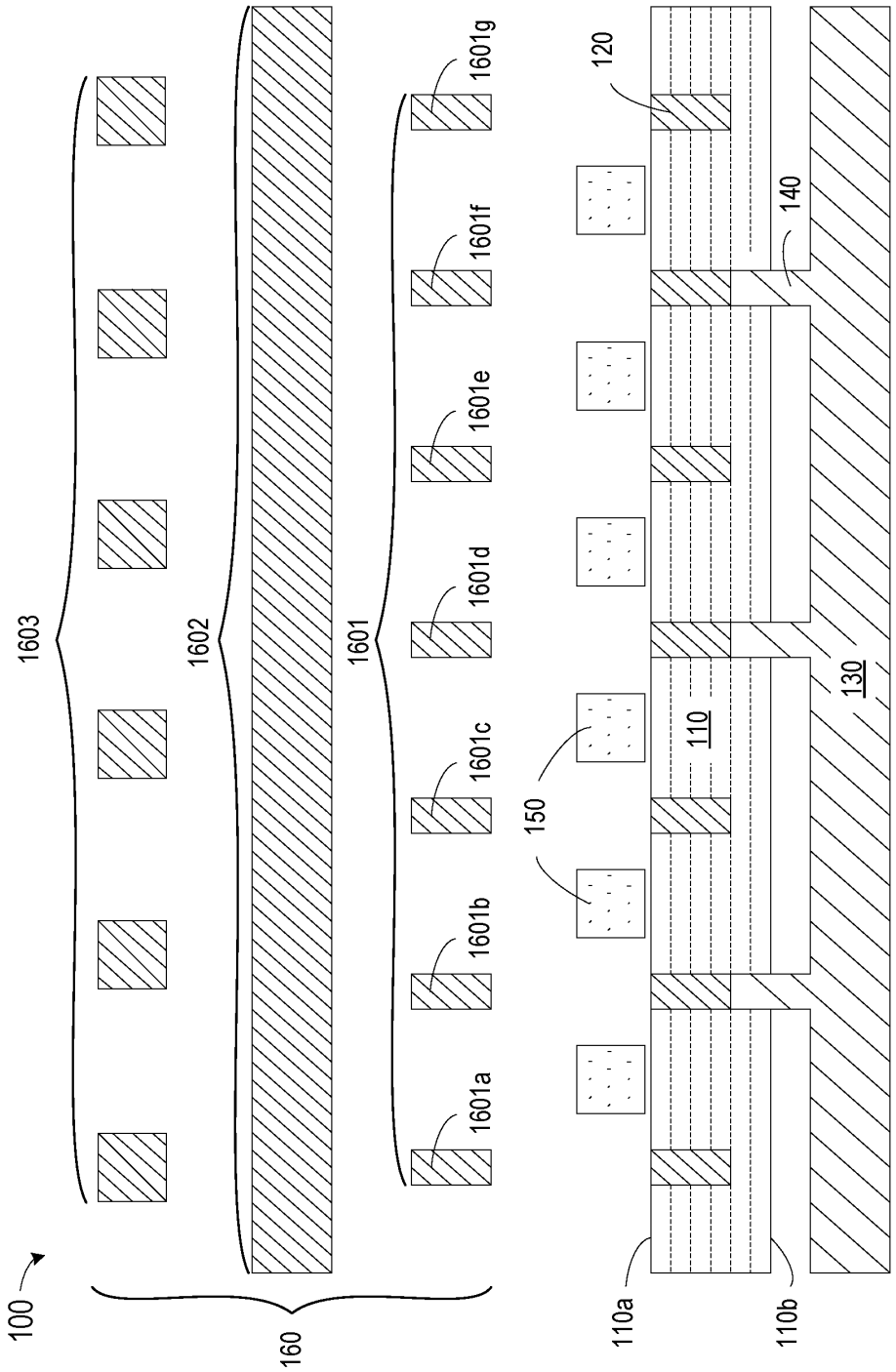

100
160
1603
1602
1601
1601a
1601b
1601c
1601d
1601e
1601f
1601g
120
140
130
110
150
110a
110b

FIG. 1

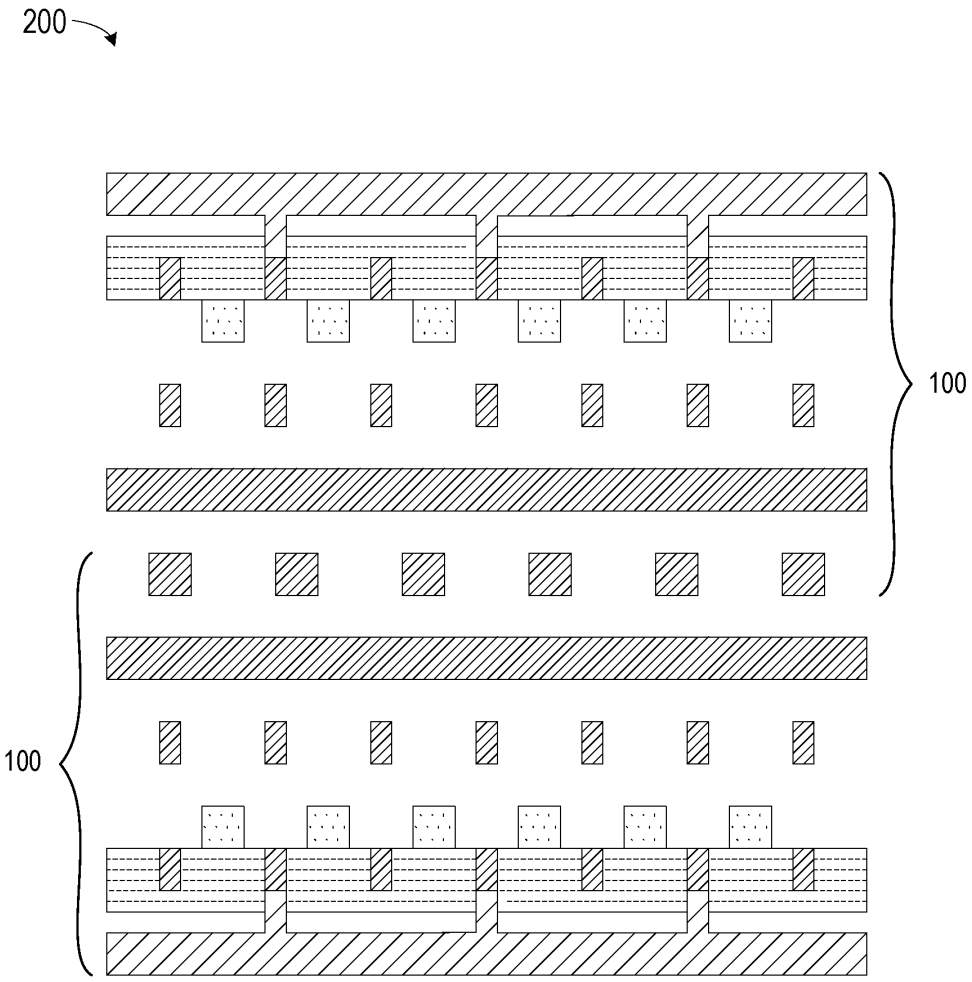


FIG. 2

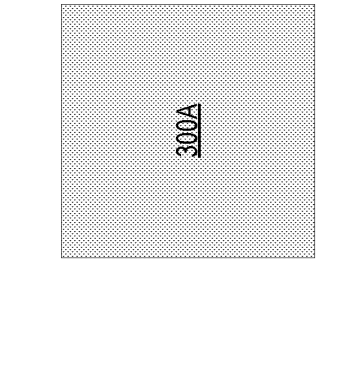


FIG. 3A

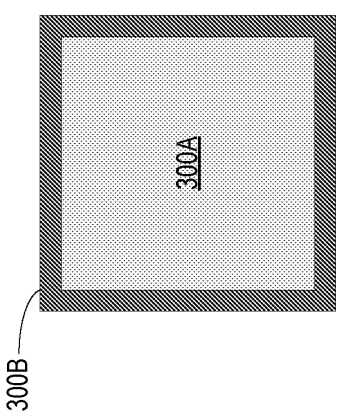


FIG. 3B

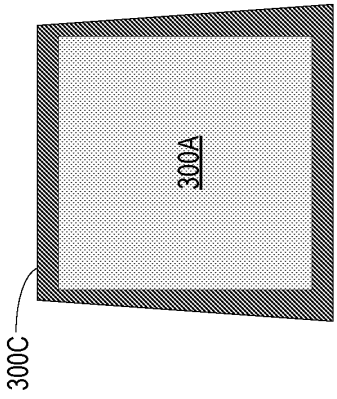


FIG. 3C

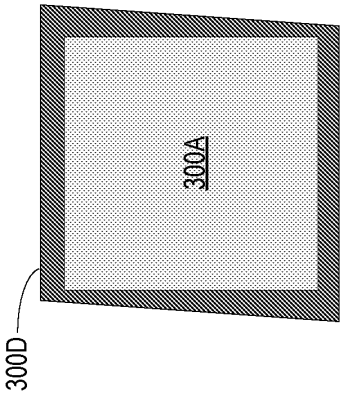


FIG. 3D

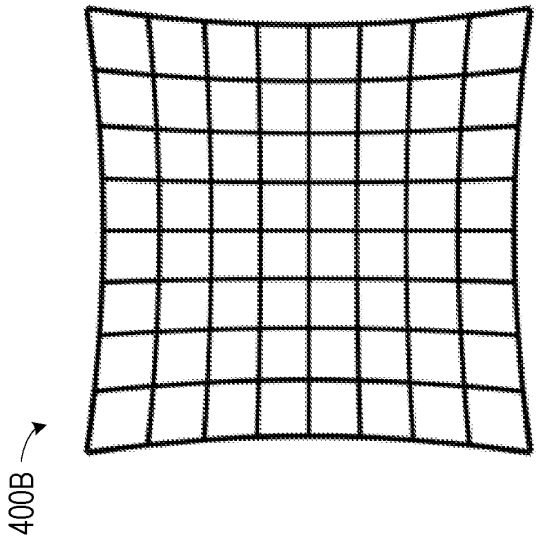


FIG. 4B

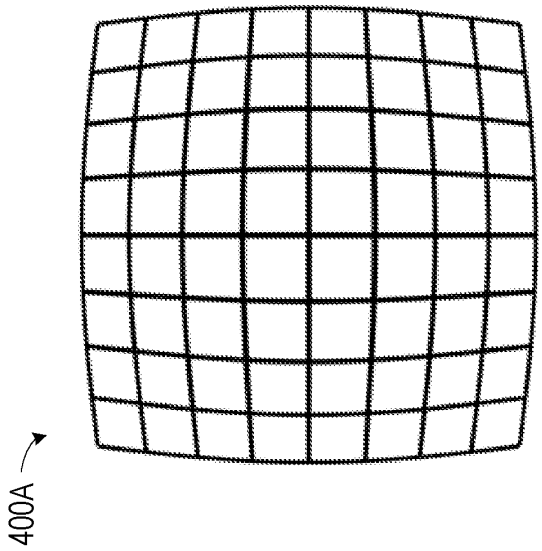


FIG. 4A

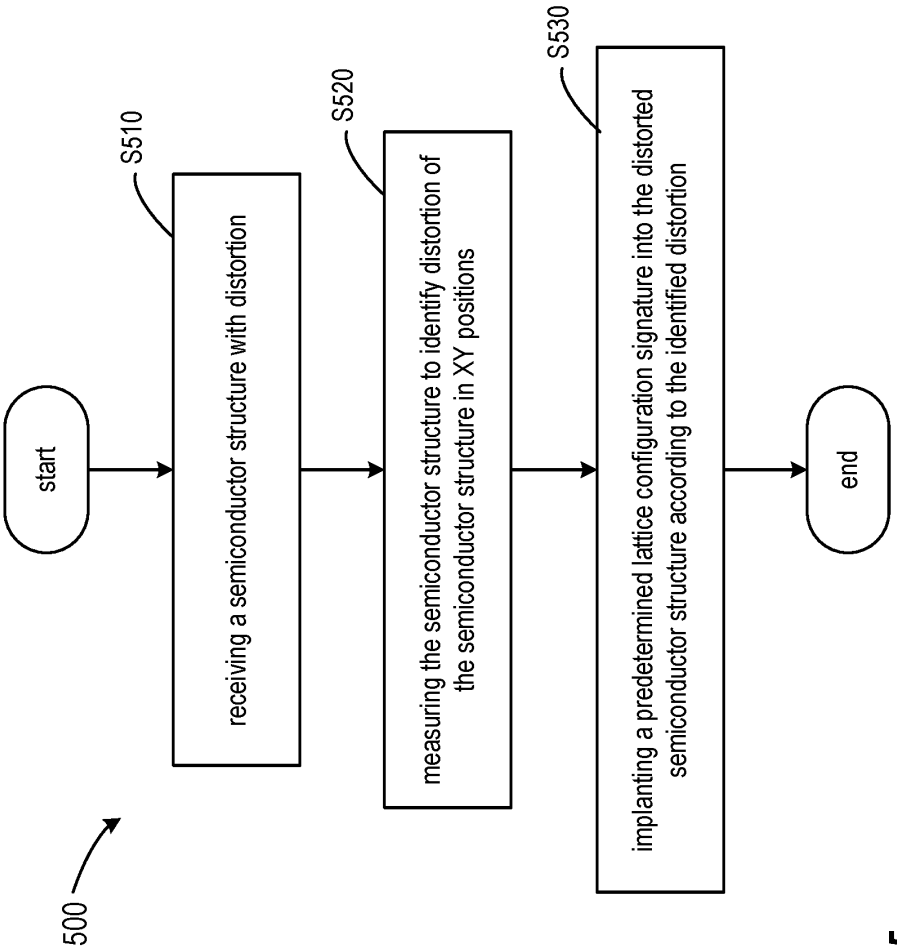

500
start
S510
receiving a semiconductor structure with distortion
S520
measuring the semiconductor structure to identify distortion of the semiconductor structure in XY positions
S530
implanting a predetermined lattice configuration signature into the distorted semiconductor structure according to the identified distortion
end

FIG. 5

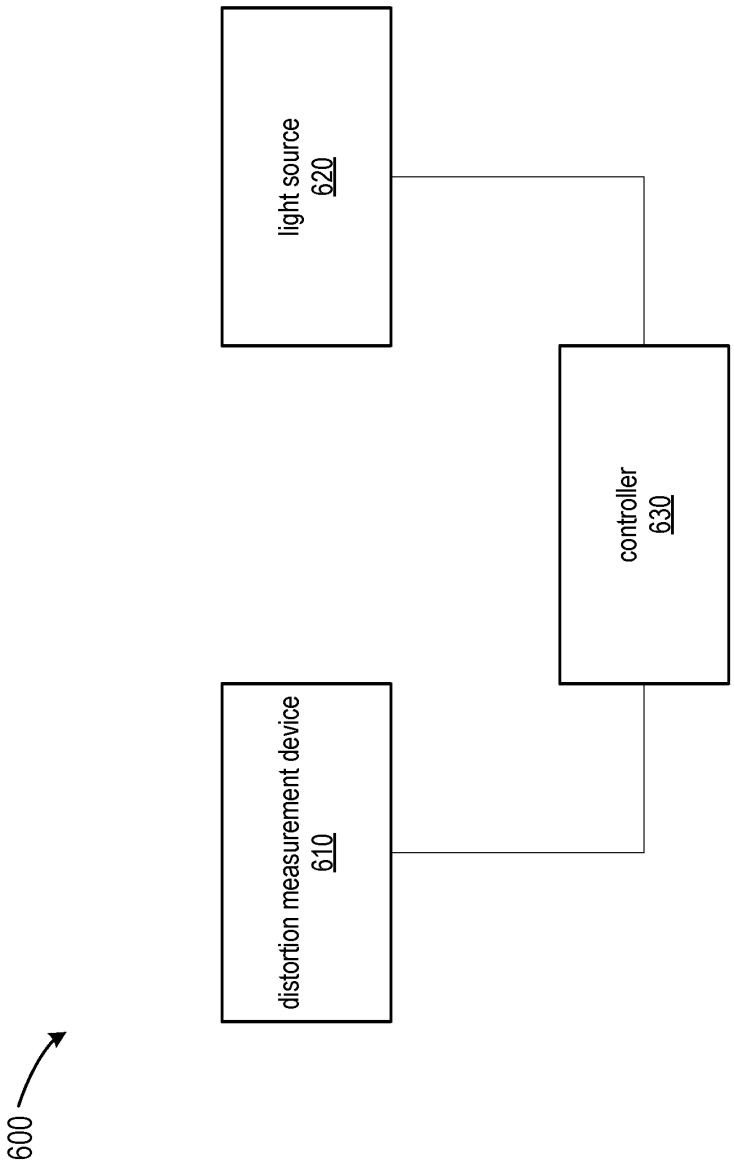

light source
620
controller
630
distortion measurement device
610
600

FIG. 6